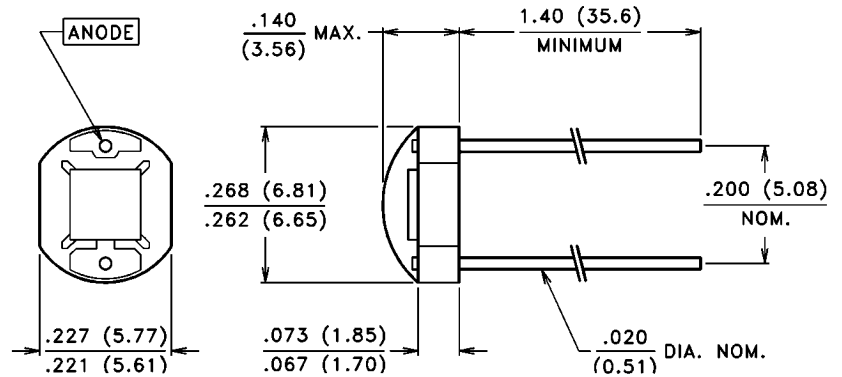


PACKAGE DIMENSIONS inch (mm)



CASE 11 CERAMIC
CHIP ACTIVE AREA: .012 in² (7.45 mm²)

PRODUCT DESCRIPTION

Planar silicon photodiode mounted on a two lead ceramic substrate and coated with a thick layer of clear epoxy. These diodes exhibit low dark current under reverse bias and fast speed of response.

ABSOLUTE MAXIMUM RATINGS

Storage Temperature: -20°C to 75°C
Operating Temperature: -20°C to 75°C

RoHS Compliant



ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTP curves, pages 45-46)

| SYMBOL | CHARACTERISTIC | TEST CONDITIONS | VTP8350H | | | UNITS |
|--------------------|---|------------------------------|----------|--------------------------------|------|------------------------|
| | | | Min. | Typ. | Max. | |
| I _{SC} | Short Circuit Current | H = 100 fc, 2850 K | 65 | 80 | | μA |
| TC I _{SC} | I _{SC} Temperature Coefficient | 2850 K | | .20 | | %/°C |
| V _{OC} | Open Circuit Voltage | H = 100 fc, 2850 K | | 350 | | mV |
| TC V _{OC} | V _{OC} Temperature Coefficient | 2850 K | | -2.0 | | mV/°C |
| I _D | Dark Current | H = 0, V _R = 10 V | | | 30 | nA |
| R _{SH} | Shunt Resistance | H = 0, V = 10 mV | | 100 | | GΩ |
| C _J | Junction Capacitance | H = 0, V = 3 V | | | 50 | pF |
| Re | Responsivity | 940 nm | | .06 | | A/(W/cm ²) |
| S _R | Sensitivity | @ Peak | | .55 | | A/W |
| λ _{range} | Spectral Application Range | | 400 | | 1150 | nm |
| λ _p | Spectral Response - Peak | | | 925 | | nm |
| V _{BR} | Breakdown Voltage | | 33 | 140 | | V |
| θ _{1/2} | Angular Resp. - 50% Resp. Pt. | | | ±60 | | Degrees |
| NEP | Noise Equivalent Power | | | 1.8 x 10 ⁻¹³ (Typ.) | | W/√Hz |
| D* | Specific Detectivity | | | 1.5 x 10 ¹² (Typ.) | | cm√Hz/W |

VTP Process Photodiodes

VTP PROCESS FAST RESPONSE, HIGH DARK RESISTANCE

FEATURES

- *Visible to enhanced IR spectral range*
- *Integral visible rejection filters available*
- *Response @ 940 nm, 0.60 A/W, typical*
- *-1 to 2% linearity over 7 to 9 decades*
- *Low dark currents*
- *High shunt resistance*
- *High reverse voltage rating*
- *Low capacitance*

PRODUCT DESCRIPTION

Photodiodes in this series have been designed for low junction capacitance. The lower the capacitance, the faster the response of the diode. Also, speed can be further increased by reverse biasing the diodes which lowers the capacitance even more.

These diodes have excellent response in the IR region and are well matched to IR LEDs. Responsivity is categorized at 940 nm (GaAs LED). Some diodes are available in packages which incorporate a visible rejection filter effectively blocking any light below 700 nm.

Diodes made with the VTP process are suitable for operation under reverse bias conditions but may be used in the photovoltaic mode. Typical reverse breakdown voltages are around 140 V. Low dark currents under reverse bias are also a feature of this series.